

# BFG325W/XR

## NPN 14 GHz wideband transistor

Rev. 2 — 15 September 2011

Product data sheet

## 1. Product profile

### 1.1 General description

NPN silicon planar epitaxial transistor in a 4-pin dual-emitter SOT343R plastic package.

### 1.2 Features and benefits

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability

### 1.3 Applications

- Intended for Radio Frequency (RF) front end applications in the GHz range, such as:
  - ◆ analog and digital cellular telephones
  - ◆ cordless telephones (Cordless Telephone (CT), Personal Communication Network (PCN), Digital Enhanced Cordless Telecommunications (DECT), etc.)
  - ◆ radar detectors
  - ◆ pagers
  - ◆ Satellite Antenna TeleVision (SATV) tuners

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	-	15	V
$V_{CEO}$	collector-emitter voltage	open base	-	-	6	V
$I_C$	collector current (DC)		-	-	35	mA
$P_{tot}$	total power dissipation	$T_{sp} \leq 90\text{ °C}$	<a href="#">[1]</a>	-	210	mW
$h_{FE}$	DC current gain	$I_C = 15\text{ mA}$ ; $V_{CE} = 3\text{ V}$ ; $T_J = 25\text{ °C}$	60	100	200	
$C_{CBS}$	collector-base capacitance	$V_{CB} = 5\text{ V}$ ; $f = 1\text{ MHz}$ ; emitter grounded	-	0.27	0.4	pF
$f_T$	transition frequency	$I_C = 15\text{ mA}$ ; $V_{CE} = 3\text{ V}$ ; $f = 1\text{ GHz}$ ; $T_{amb} = 25\text{ °C}$	-	14	-	GHz



Table 1. Quick reference data ...continued

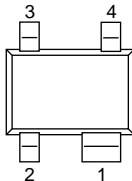
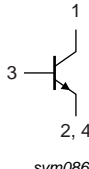
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$G_{\max}$	maximum power gain <sup>[2]</sup>	$I_C = 15 \text{ mA}$ ; $V_{CE} = 3 \text{ V}$ ; $f = 1.8 \text{ GHz}$ ; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	-	18.3	-	dB
$ S_{21} ^2$	insertion power gain	$I_C = 15 \text{ mA}$ ; $V_{CE} = 3 \text{ V}$ ; $f = 1.8 \text{ GHz}$ ; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$ ; $Z_S = Z_L = 50 \text{ } \Omega$	-	14	-	dB
NF	noise figure	$\Gamma_S = \Gamma_{\text{opt}}$ ; $I_C = 3 \text{ mA}$ ; $V_{CE} = 3 \text{ V}$ ; $f = 2 \text{ GHz}$	-	1.1	-	dB

[1]  $T_{\text{sp}}$  is the temperature at the soldering point of the collector pin.

[2]  $G_{\max}$  is the maximum power gain, if  $K > 1$ . If  $K < 1$  then  $G_{\max} = \text{MSG}$ , see [Figure 4](#).

## 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	collector		 sym086
2	emitter		
3	base		
4	emitter		

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BFG325W/XR	-	plastic surface mounted package; reverse pinning; 4 leads	SOT343R

## 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
BFG325W/XR	A8*

[1] \* = p: made in Hong Kong.

## 5. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	15	V
$V_{CEO}$	collector-emitter voltage	open base	-	6	V
$V_{EBO}$	emitter-base voltage	open collector	-	2	V
$I_C$	collector current (DC)		-	35	mA
$P_{tot}$	total power dissipation	$T_{sp} \leq 90\text{ °C}$	[1]	210	mW
$T_{stg}$	storage temperature		-65	+175	°C
$T_j$	junction temperature		-	175	°C

[1]  $T_{sp}$  is the temperature at the soldering point of the collector pin.

## 6. Thermal characteristics

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	$T_{sp} \leq 90\text{ °C}$	[1]	403 K/W

[1]  $T_{sp}$  is the temperature at the soldering point of the collector pin.

## 7. Characteristics

**Table 7. Characteristics**

$T_j = 25\text{ °C}$ ; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{CBO}$	collector-base cut-off current	$I_E = 0\text{ A}$ ; $V_{CB} = 5\text{ V}$	-	-	15	nA
$h_{FE}$	DC current gain	$I_C = 15\text{ mA}$ ; $V_{CE} = 3\text{ V}$	60	100	200	
$C_{CBS}$	collector-base capacitance	$V_{CB} = 5\text{ V}$ ; $f = 1\text{ MHz}$ ; emitter grounded	-	0.27	0.4	pF
$C_{CES}$	collector-emitter capacitance	$V_{CE} = 5\text{ V}$ ; $f = 1\text{ MHz}$ ; base grounded	-	0.22	-	pF
$C_{EBS}$	emitter-base capacitance	$V_{EB} = 0.5\text{ V}$ ; $f = 1\text{ MHz}$ ; collector grounded	-	0.49	-	pF
$f_T$	transition frequency	$I_C = 15\text{ mA}$ ; $V_{CE} = 3\text{ V}$ ; $f = 1\text{ GHz}$ ; $T_{amb} = 25\text{ °C}$	-	14	-	GHz
$G_{max}$	maximum power gain[1]	$I_C = 15\text{ mA}$ ; $V_{CE} = 3\text{ V}$ ; $f = 1.8\text{ GHz}$ ; $T_{amb} = 25\text{ °C}$	-	18.3	-	dB
$ s_{21} ^2$	insertion power gain	$I_C = 15\text{ mA}$ ; $V_{CE} = 3\text{ V}$ ; $T_{amb} = 25\text{ °C}$ ; $Z_S = Z_L = 50\text{ }\Omega$				
		$f = 1.8\text{ GHz}$	-	14	-	dB
		$f = 3\text{ GHz}$	-	10	-	dB
NF	noise figure	$\Gamma_s = \Gamma_{opt}$ ; $I_C = 3\text{ mA}$ ; $V_{CE} = 3\text{ V}$ ; $f = 2\text{ GHz}$	-	1.1	-	dB
$P_{L(1dB)}$	output power at 1 dB gain compression	$I_C = 15\text{ mA}$ ; $V_{CE} = 3\text{ V}$ ; $f = 1.8\text{ GHz}$ ; $T_{amb} = 25\text{ °C}$ ; $Z_S = Z_L = 50\text{ }\Omega$	-	8.7	-	dBm
IP3	third order intercept point	$I_C = 15\text{ mA}$ ; $V_{CE} = 3\text{ V}$ ; $f = 1.8\text{ GHz}$ ; $T_{amb} = 25\text{ °C}$ ; $Z_S = Z_L = 50\text{ }\Omega$	-	19.4	-	dBm

[1]  $G_{\max}$  is the maximum power gain, if  $K > 1$ . If  $K < 1$  then  $G_{\max} = \text{MSG}$ , see [Figure 4](#).

$K$  is the Rollet stability factor: 
$$K = \frac{1 + |Ds|^2 - |s_{11}|^2 - |s_{22}|^2}{2 \times |s_{21}| \times |s_{12}|}$$
 where  $Ds = s_{11} \times s_{22} - s_{12} \times s_{21}$ .

MSG = maximum stable gain.

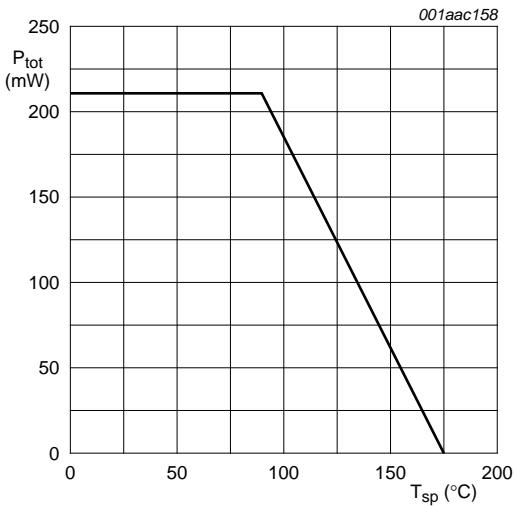


Fig 1. Power derating curve

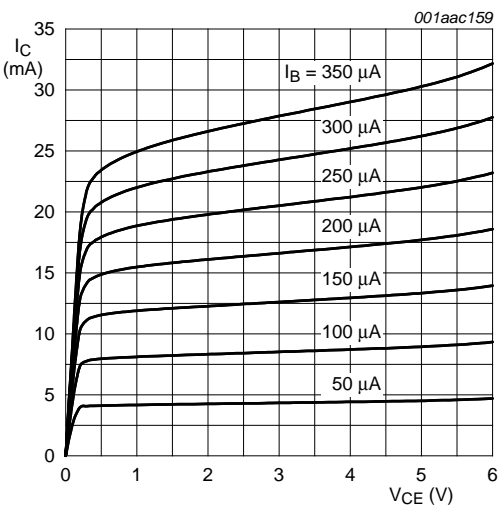
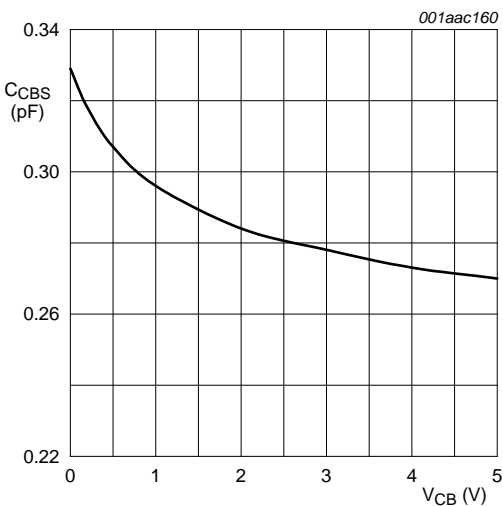
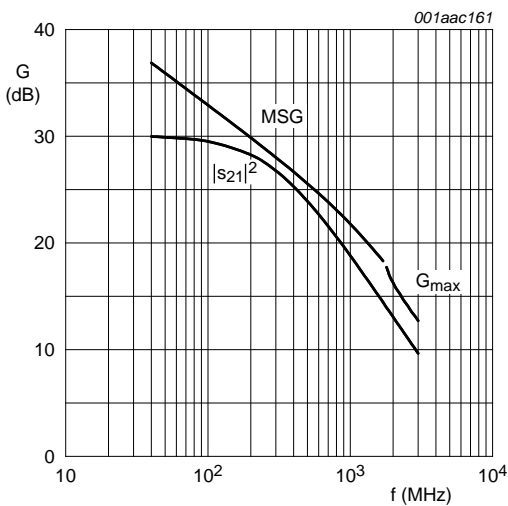


Fig 2. Collector current as a function of collector-emitter voltage; typical values



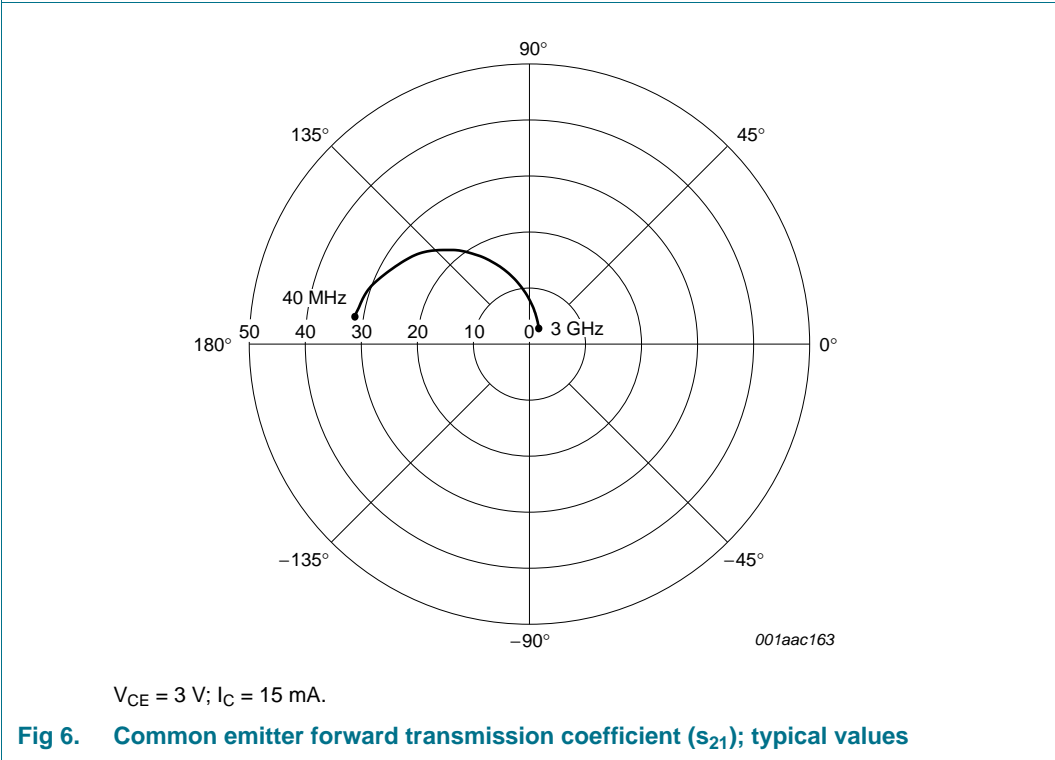
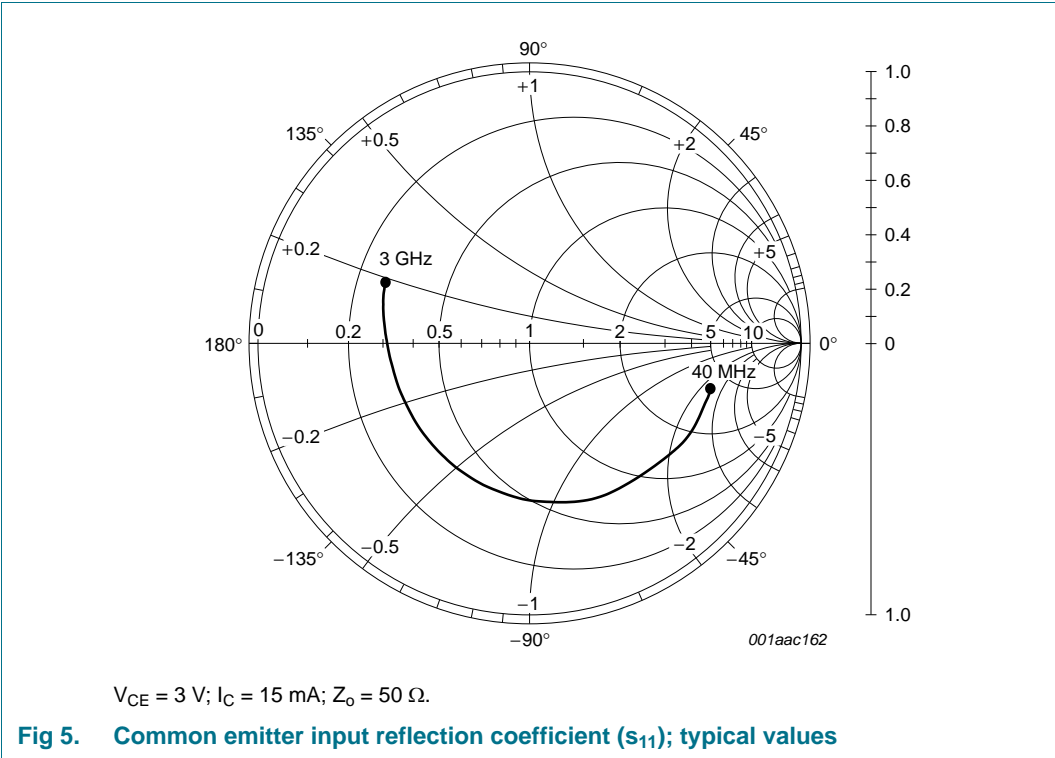
$I_C = 0 \text{ mA}; f = 1 \text{ MHz}.$

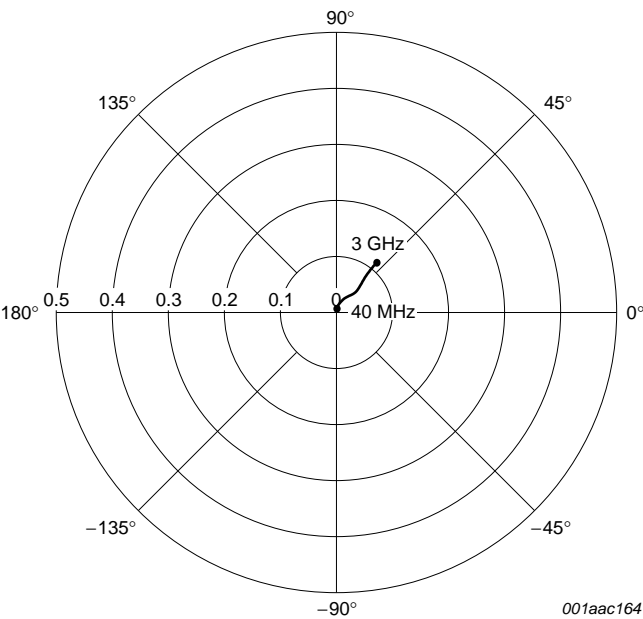
Fig 3. Collector-base capacitance as a function of collector-base voltage; typical values



$I_C = 15 \text{ mA}; V_{\text{CE}} = 3 \text{ V}.$

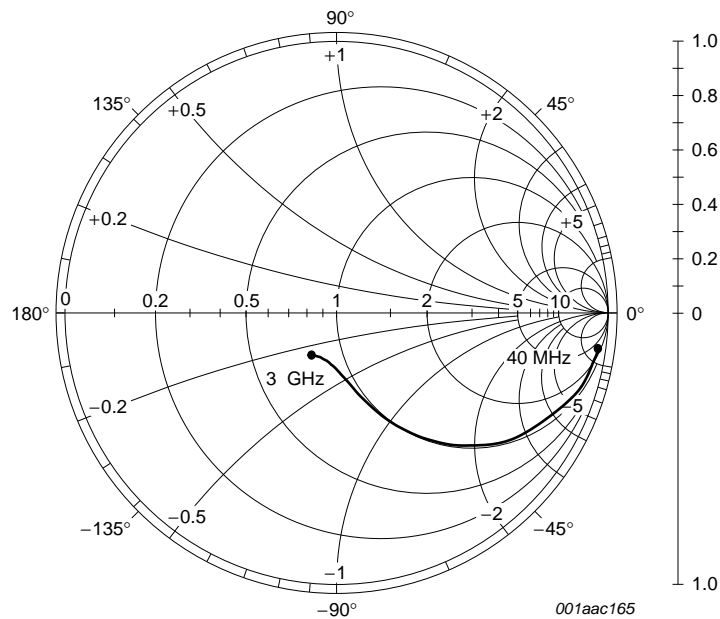
Fig 4. Gain as a function of frequency; typical values





$V_{CE} = 3\text{ V}; I_C = 15\text{ mA}.$

Fig 7. Common emitter reverse transmission coefficient ( $s_{12}$ ); typical values



$V_{CE} = 3\text{ V}; I_C = 15\text{ mA}; Z_o = 50\text{ }\Omega.$

Fig 8. Common emitter output reflection coefficient ( $s_{22}$ ); typical values

## 8. Application information

**Table 8. SPICE parameters of the BFG325 DIE**

Sequence	Parameter	Value	Unit
1	IS	26.6	aA
2	BF	200	-
3	NF	1	-
4	VAF	40	V
5	IKF	105	mA
6	ISE	2.3	fA
7	NE	2.114	-
8	BR	10	-
9	NR	1	-
10	VAR	2.5	V
11	IKR	10	A
12	ISC	0	aA
13	NC	1.5	-
14	RB	3.6	$\Omega$
15	RE	1.5	$\Omega$
16	RC	2.6	$\Omega$
17	CJE	185.6	fF
18	VJE	890	mV
19	MJE	0.294	-
20	CJC	77.06	fF
21	VJC	601	mV
22	MJC	0.159	-
23	XCJC	1	-
24	FC	0.7	-
25	TF	8.1	ps
26	XTF	10	-
27	VTF	1000	V
28	ITF	150	mA
29	PTF	0	deg
30	TR	0	ns
31	KF	0	-
32	AF	1	-
33	TNOM	25	$^{\circ}\text{C}$
34	EG	1.014	eV
35	XTB	0	-
36	XTI	8	-
37	Q1.AREA	2.5	-

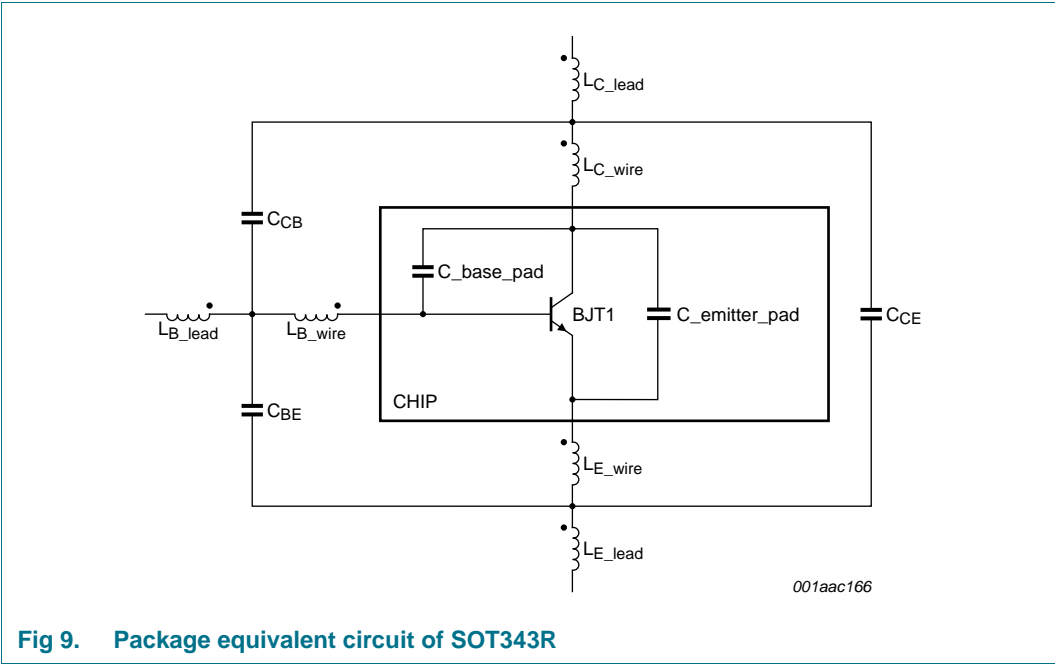


Fig 9. Package equivalent circuit of SOT343R

Table 9. List of components; see [Figure 9](#)

Designation	Value	Unit
$C_{CB}$	2	fF
$C_{BE}$	80	fF
$C_{CE}$	80	fF
$C_{base\_pad}$	67	fF
$C_{emitter\_pad}$	142	fF
$L_{C\_wire}$	0.767	nH
$L_{B\_wire}$	0.842	nH
$L_{E\_wire}$	0.212	nH
$L_{C\_lead}$	0.28	nH
$L_{B\_lead}$	0.281	nH
$L_{E\_lead}$	0.1	nH



9. Package outline

Plastic surface-mounted package; reverse pinning; 4 leads

SOT343R

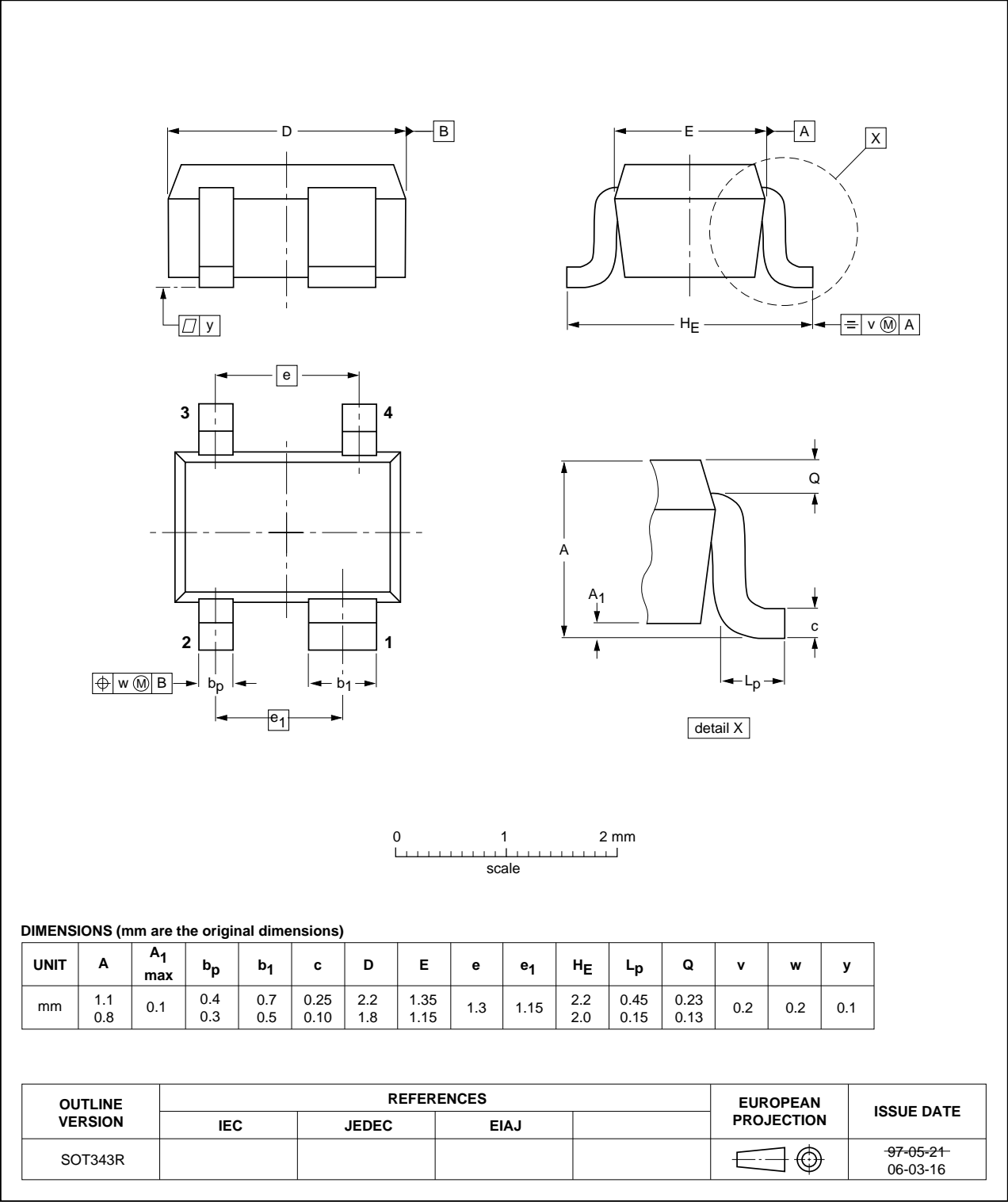


Fig 10. Package outline SOT343R

## 10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BFG325W_XR v.2	20110915	Product data sheet	-	BFG325W_XR v.1
Modifications:	<ul style="list-style-type: none"><li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>• Legal texts have been adapted to the new company name where appropriate.</li><li>• Package outline drawings have been updated to the latest version.</li></ul>			
BFG325W_XR v.1 (9397 750 14246)	20050202	Product data sheet	-	-

## 11. Legal information

### 11.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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